REMARKS

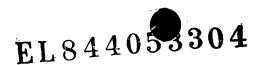
Claims 21-63 are presented herein for examination. Claims 21-56 were withdrawn from consideration in the immediate parent application as being non-elected species of a first invention, the Examiner alleging that there was no generic Claim. A copy of the Restriction is provided herewith as Attachment 'A'. Claims 57-63 are new Claims directed to the invention and species of Claims 29-41. Such new Claims are fully supported by the specification and accompanying figures. For example, Figs. 2-4 and the associated text in the specification. In addition, Applicant has amended both the Title and the Abstract of the Disclosure.

Respectfully submitted,

Dated.

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Reg. No. 37,279



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No.	09/641,879
Priority Filing Date	August 17, 2000
Inventor	Brenda D. Kraus et al.
Assignee	Micron Technology, Inc.
Priority Group Art Unit	2813
Priority Examiner	Y. Huyhn
Attorney's Docket No	MI22-1859
Title: DRAM Circuitry, Method Of Forming A Field E	Emission Device, And Field
Emission Device (As Amended)	

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING PRELIMINARY AMENDMENT

The Title is amended as follows. <u>Underlines</u> indicate insertions and strikeouts indicate deletions.

Method Of Depositing An Aluminum Nitride Comprising Layer Over A
Semiconductor Substrate, Method Of Forming DRAM Circuitry, DRAM Circuitry,
Method Of Forming A Field Emission Device, And Field Emission Device

The Abstract of the Disclosure is amended as follows. <u>Underlines</u> indicate insertions and strikeouts indicate deletions.

The invention is a method of depositing an aluminum nitride comprising layer over a semiconductor substrate, a method of forming DRAM circuitry, DRAM circuitry, a method of forming a field emission device, and a field emission device. In one aspect, a method of depositing Depositing an aluminum nitride comprising layer over a semiconductor substrate includes positioning a

semiconductor substrate within a chemical vapor deposition reactor. Ammonia and at least one of triethylaluminum and trimethylaluminum are fed to the reactor while the substrate is at a temperature of about 500°C or less and at a reactor pressure from about 100 mTorr to about 725 Torr effective to deposit a layer comprising aluminum nitride over the substrate at such temperature and reactor pressure. In one aspect, such layer is utilized as a cell dielectric layer in DRAM circuitry.—In one aspect, such Such layer is deposited over emitters of a field emission display. The invention contemplates DRAM and field emission devices utilizing such layer and alternate layers.

The Claims have been amended as follows. <u>Underlines</u> indicate insertions and strikeouts indicate deletions.

Cancel Claims 1-20.

Add Claims 57-63.